

2MBI300VN-120-50

IGBT Modules

IGBT MODULE (V series) 1200V / 300A / 2 in one package

Features

High speed switching Voltage drive Low Inductance module structure

Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items			Symbols	Conditions		Maximum ratings	Units	
	Collector-Emitter voltage		Vces			1200	V	
Inverter	Gate-Emitter voltage		V _{GES}			±20	V	
			Ic	Continuous	Tc=25°C	450		
	Collector current	Tc=100°C			300			
		Ic pulse	1ms		600	Α		
			-lc				300	
			-lc pulse	1ms			600	
	Collector power dissipation		Pc	1 device		1595	W	
Junction temperature			Tj			175		
Operating junction temperature (under switching conditions)			Tjop			150	°C	
Case temperature			Tc		,	125		
St	Storage temperature		Tstg			-40 to +125		
Isc		between terminal and copper base (*1)	V _{iso}	AC : 1min.		2500	VAC	
		between thermistor and others (*2)	V iso			2500	VAC	
8.	rew torque	Mounting (*3)				3.5	N m	
30		Terminals (*4)	-			4.5	IN III	

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value: Mounting: 2.5-3.5 Nm (M5) Note *4: Recommendable value: Terminals: 3.5-4.5 Nm (M6)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

14.		Cumbala	Conditions		Characteristics			Units		
Items		Symbols	Conditions		min.	typ.	max.	Units		
	Zero gate voltage collector current	Ices	V _{GE} = 0V, V _{CE} = 1200V		-	-	3.0	mA		
	Gate-Emitter leakage current	Iges	$V_{CE} = 0V$, $V_{GE} = \pm 20V$		-	-	600	nA		
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 300mA		6.0	6.5	7.0	V		
	Collector-Emitter saturation voltage	V	V _{GE} = 15V I _C = 300A	Tj=25°C	-	2.20	2.65	V		
		VCE (sat)		Tj=125°C	-	2.50	-			
		(terminal)		Tj=150°C	-	2.55	-			
		V		Tj=25°C	-	1.75	2.20			
		V _{CE} (sat)		Tj=125°C	-	2.05	-			
		(chip)		Tj=150°C	-	2.10	-			
ē	ernal gate resistance Rg(int) -		-	2.5	-	Ω				
	Input capacitance	Cies	$V_{CE} = 10V, V_{GE} = 0V, f = 1MHz$		-	27	-	nF		
nverte	Turn-on time	ton	Vcc = 600V	-	-	550	-	nsec		
≥		tr	Ic = 300A		-	180	-			
_		tr (i)	V _{GE} = ±15V		-	120	-			
	Turn-off time	toff	$R_{\rm G} = 0.93\Omega$		-	1050	-			
		tf	L _s = 80nH		-	110	-			
	Forward on voltage	VF		Tj=25°C	-	2.15	2.60			
		1 - 1		Tj=125°C	-	2.30	-			
		(terminal)	V _{GE} = 0V	Ti=150°C	-	2.25	-			
			I _F = 300A	Tj=25°C	-	1.70	2.15			
		V _F		Tj=125°C	-	1.85	-			
		(chip)		Ti=150°C	-	1.80	-			
	Reverse recovery time trr IF = 300A		I _F = 300A		-	200	-	nsec		
to		Ь	T=25°C T=100°C		-	5000	-	Ω		
Thermistor	Resistance	R			465	495	520			
를	B value	В	T=25/50°C		3305	3375	3450	K		

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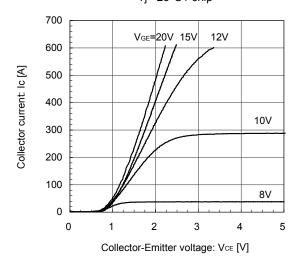
● Thermal resistance characteristics

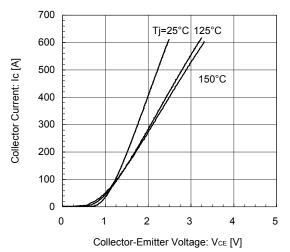
Items	Symbols	Conditions	Characteristics			Units
ills		Conditions	min.	typ.	max.	Units
Thermal resistance (1device)	Rth(j-c)	Inverter IGBT	-	-	0.094	°C/W
nermai resistance (ruevice)		Inverter FWD	-	-	0.150	
Contact thermal resistance (1device) (*5)	Rth(c-f)	with Thermal Compound	-	0.0167	-	

Note $^{\star}5$: This is the value which is defined mounting on the additional cooling fin with thermal compound.

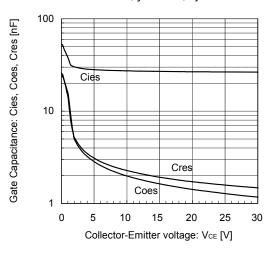
■ Characteristics (Representative)

 $[INVERTER] \\ Collector current vs. Collector-Emitter voltage (typ.) \\ Tj= 25 ^{\circ}C \ / \ chip$

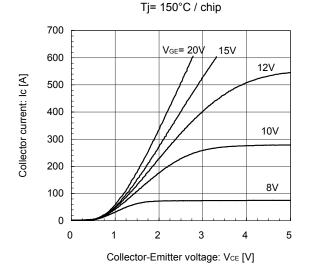




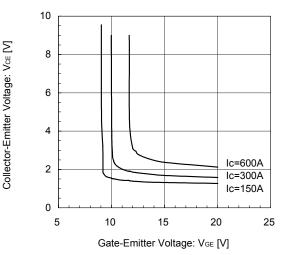
[INVERTER]
Gate Capacitance vs. Collector-Emitter Voltage (typ.) $V_{\rm GE} = 0 \text{V}, \ f = 1 \text{MHz}, \ \text{Tj} = 25 ^{\circ} \text{C}$



[INVERTER]
Collector current vs. Collector-Emitter voltage (typ.)



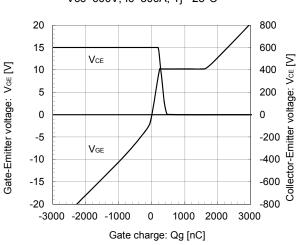
 $[INVERTER] \\ Collector-Emitter voltage \ vs. \ Gate-Emitter voltage \ (typ.) \\ Tj= 25^{\circ}C \ / \ chip$



[INVERTER]

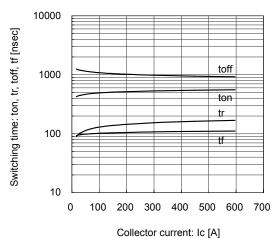
Dynamic Gate Charge (typ.)

Vcc=600V, Ic=300A, Tj= 25°C



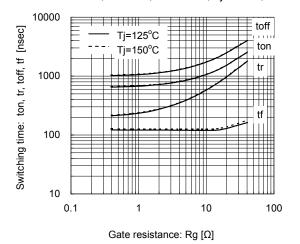
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=25°C



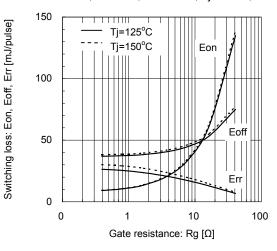
[INVERTER]

Switching time vs. Gate resistance (typ.) Vcc=600V, Ic=300A, V_{GE}=±15V, Tj=125°C, 150°C



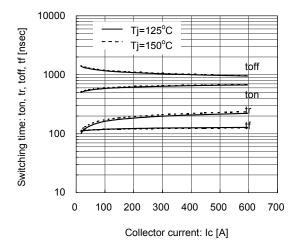
[INVERTER]

Switching loss vs. Gate resistance (typ.) Vcc=600V, Ic=300A, V_{GE}=±15V, Tj=125°C, 150°C



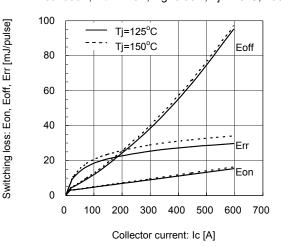
[INVERTER]

Switching time vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=125°C, 150°C



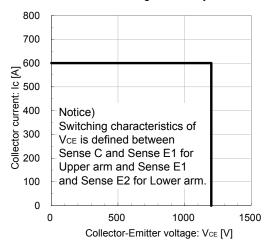
[INVERTER]

Switching loss vs. Collector current (typ.) Vcc=600V, VgE= \pm 15V, Rg=0.93 Ω , Tj=125°C, 150°C



[INVERTER]

Reverse bias safe operating area (max.) +V_{GE}=15V, -V_{GE}=15V, Rg=0.93 Ω , Tj=150°C

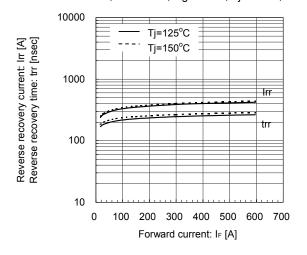


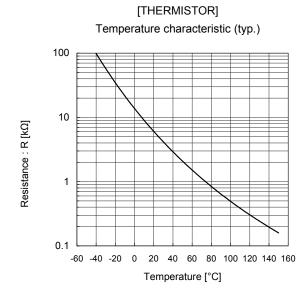
Forward current: I_F [A]

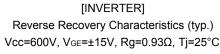
[INVERTER] Forward Current vs. Forward Voltage (typ.) 700 600 Tj=25°C 500 400 300 125 °C 200 100

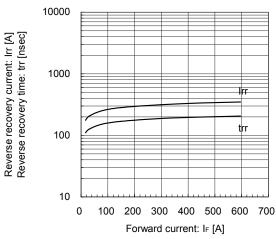
0 0 2 Forward on voltage: V_F [V]

[INVERTER] Reverse Recovery Characteristics (typ.) Vcc=600V, VGE=±15V, Rg=0.93Ω, Tj=125°C, 150°C

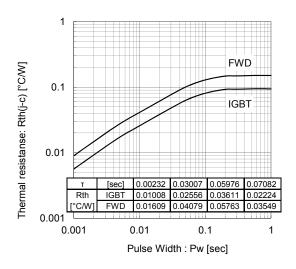




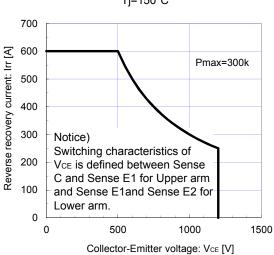




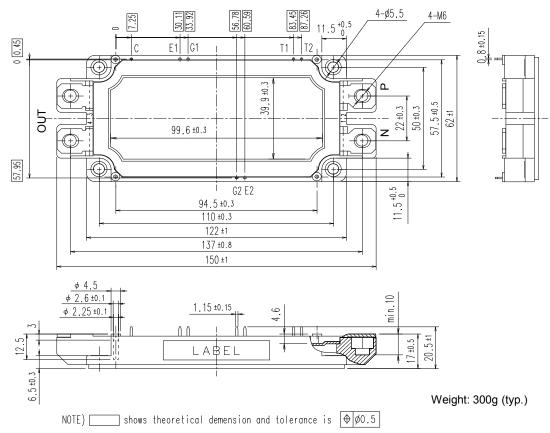
Transient Thermal Resistance (max.)



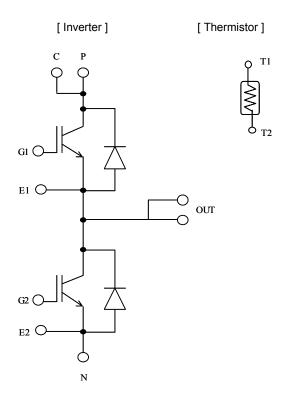
FWD safe operating area (max.) Tj=150°C



■ Outline Drawings (Unit : mm)



■ Equivalent Circuit



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- Communications equipment (terminal devices)
- Measurement equipment

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- Audiovisual equipment
- Electrical home appliances
- Personal equipment
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Traffic-signal control equipment

- Gas leakage detectors with an auto-shut-off feature
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- Safety devices

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IGBT Modules

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